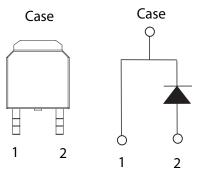
Littelfuse Power

## GEN2 SiC Schottky Diode LSIC2SD065C10A, 650 V, 10 A, TO-252-2L (DPAK)

# LSIC2SD065C10A 650 V, 10 A SiC Schottky Barrier Diode



#### Circuit Diagram TO-252-2L (DPAK)



### Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

HF

• Excellent surge capability

temperature-independent

switching behavior

• Dramatically reduced

compared to Si bipolar

switching losses

EV charging stations

Extremely fast,

RoHS

Po

#### Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature

#### Applications

- Boost diodes in PFC or DC/DC stages
- Solar invertersIndustrial motor drives

diodes

- Switch-mode power supplies
- Uninterruptible power supplies

#### Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

#### **Maximum Ratings**

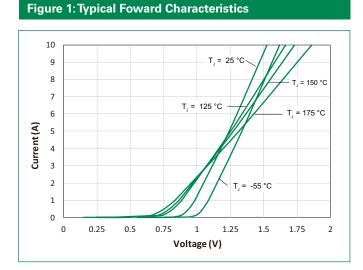
Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	-	650	V	
DC Blocking Voltage	V <sub>R</sub>	T <sub>J</sub> = 25 °C	650	V	
		T <sub>c</sub> = 25 °C	27	A	
Continuous Forward Current	I <sub>F</sub>	T <sub>c</sub> = 135 °C	12.5		
		$T_c = 147 \text{ °C}$	10		
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	$T_c = 25 \text{ °C}, T_p = 10 \text{ ms}, \text{ Half sine pulse}$	48	A	
Power Dissipation	D	$T_c = 25 \text{ °C}$	100	۱۸/	
	P <sub>Tot</sub>	$T_c = 110 \text{ °C}$	43		
Operating Junction Temperature	TJ	-	-55 to 175	°C	
Storage Temperature	T <sub>stg</sub>	-	-55 to 150	°C	
Soldering Temperature (reflow MSL1)	T <sub>sold</sub>	-	260	°C	

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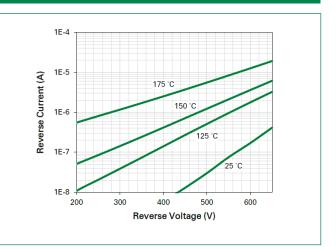
Electrical Characteristics							
Characteristics	Symbol	Conditions	Value				
			Min.	Тур.	Max.	Unit	
Forward Voltage		I <sub>F</sub> = 10 A, Τ <sub>J</sub> = 25 °C	-	1.5	1.8	V	
	V <sub>F</sub>	I <sub>F</sub> = 10 A, T <sub>J</sub> = 175 °C	-	1.85	-	V	
Reverse Current		$V_{_{ m R}} = 650 \text{ V}, \text{ T}_{_{ m J}} = 25 \ ^{\circ}\text{C}$	-	<1	50		
	I <sub>R</sub>	$V_{_{ m R}} = 650 \text{ V}$ , $T_{_{ m J}} = 175 \ ^{\circ}\text{C}$	-	25	-	μΑ	
Total Capacitance		$V_{R} = 1 V$ , f = 1 MHz	-	470	-		
	С	$V_{_{ m R}} = 200 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	60	-	pF	
		$V_{_{\rm R}} = 400 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	43	-		
Total Capacitive Charge	Q <sub>c</sub>	$V_{R} = 400 V$ , $Q_{c} = \int_{0}^{V_{R}} C(V) dV$	-	30	-	nC	

#### **Thermal Characteristics**

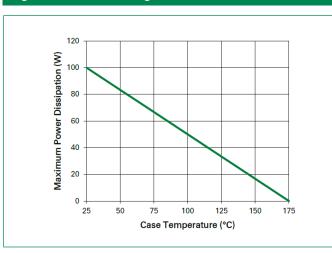
Characteristics	Symbol	Value	Unit
Thermal Resistance	R <sub>ejc</sub>	1.5	°C/W



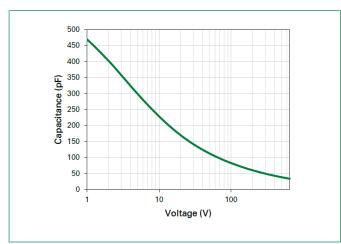
#### Figure 2: Typical Reverse Characteristics

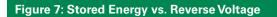


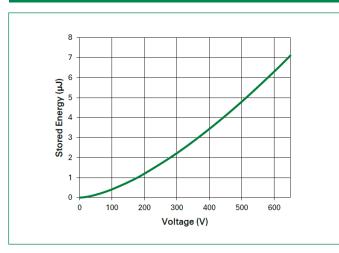
#### Figure 3: Power Derating



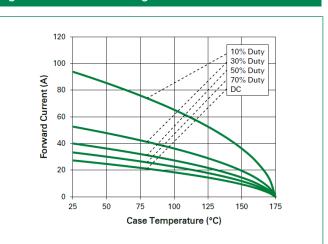
#### Figure 5: Capacitance vs. Reverse Voltage



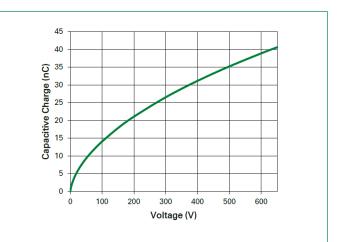




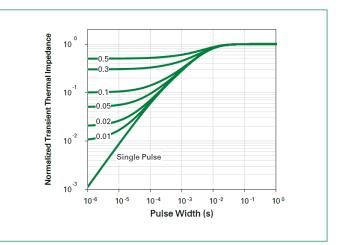
#### Figure 4: Current Derating



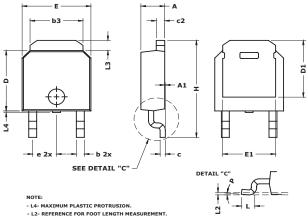
#### Figure 6: Capacitive Charge vs. Reverse Voltage



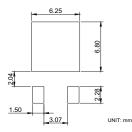
#### Figure 8: Transient Thermal Impedance



#### **Dimensions TO-252-2L (DPAK)**

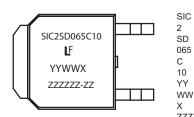


Recommended Solder Pattern Layout



Symbol	Inches			Millimeters			
Symbol	Min	Nom	Max	Min	Nom	Max	
А	0.085	0.090	0.095	2.16	2.29	2.41	
A1	0	0.003	0.005	0	0.08	0.13	
b	0.025	0.030	0.035	0.64	0.76	0.89	
b3	0.195	0.200	0.215	4.95	5.08	5.46	
С	0.018	0.020	0.024	0.46	0.51	0.61	
C2	0.018	0.032	0.035	0.46	0.81	0.89	
D	0.235	0.240	0.245	5.97	6.10	6.22	
D1	0.205	-	-	5.21	-	-	
E	0.250	0.260	0.265	6.35	6.60	6.73	
E1	0.170	-	-	4.32	-	-	
е	0.090 BSC				2.29 BSC		
Н	0.370	0.387	0.410	9.40	9.83	10.41	
L	0.040	0.045	0.050	1.02	1.14	1.27	
L2	0.010 BSC				0.25 BS	C	
L3	0.035	-	0.050	0.89	-	1.27	
L4	0	-	0.006	0	-	0.15	
Р	0°	-	8 °	0°	-	8 °	

#### Part Numbering and Marking System



SIC	= SiC Diode
	= Gen2
D	= Schottky Diode
65	= Voltage Rating (650 V)
;	= TO-252-2L (DPAK)
0	= Current Rating (10 A)
Ϋ́	= Year
V/V/	= Week

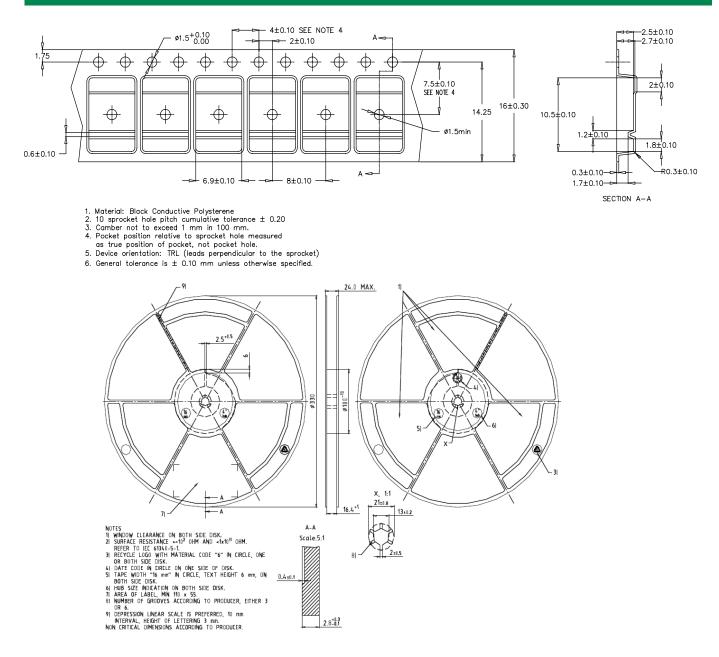
= Week

X = Special code ZZZZZZ-ZZ = Lot Number = Special code

### **Packing Options**

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD065C10A	SIC2SD065C10	Tape and Reel	2500

#### Carrier Tape & Reel Specification TO-252-2L (DPAK)



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